Product Summary

BV_{DSS}	$R_{DS(ON)}$ Max	I_D Max T_A = +25°C
20V	0.4Ω @ V_{GS} = 4.5V	1.0A
	0.5Ω @ V_{GS} = 2.5V	0.9A
	0.7Ω @ V_{GS} = 1.8V	0.8A

Features and Benefits

- Footprint of just 0.6mm^2 – Thirteen Times Smaller than SOT23
- 0.4mm Profile – Ideal for Low Profile Applications
- Low Gate Threshold Voltage
- Fast Switching Speed
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

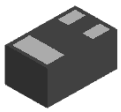
- Load Switch

Mechanical Data

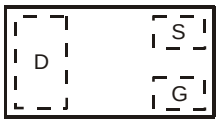
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e4
- Weight: 0.001 grams (Approximate)

ESD Protected Gate

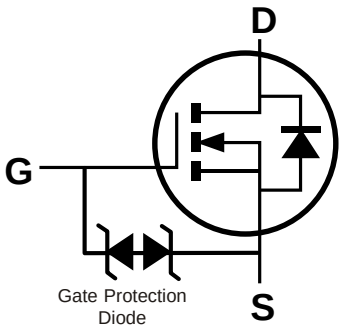
X2-DFN1006-3



Bottom View



Top View
Internal Schematic



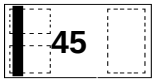
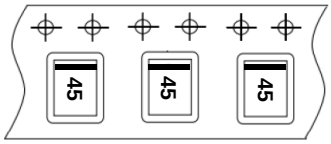
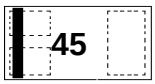
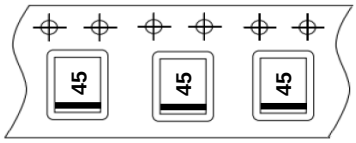
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Marking	Reel Size (inches)	Tape Width (mm)	Tape Pitch (mm)	Quantity per Reel
DMN2450UFB4-7B	45	7	8	2	10,000
DMN2450UFB4-7R	45	7	8	4	3,000

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information

DMN2450UFB4-7R	 Top View Bar Denotes Gate and Source Side 	45 = Part Marking Code
DMN2450UFB4-7B	 Top View Bar Denotes Gate and Source Side 	45 = Part Marking Code

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	20	V
Gate-Source Voltage			V_{GSS}	±12	V
Continuous Drain Current (Note 6) V_{GS} = 4.5V	Steady State	T_A = +25°C T_A = +70°C	I_D	1.0 0.8	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	3.0	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_D	0.5	W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	225	°C/W
Total Power Dissipation (Note 6)	P_D	0.9	W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	129	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	20	-	-	V	V_{GS} = 0V, I_D = 250µA
Zero Gate Voltage Drain Current T_J = +25°C	I_{DSS}	-	-	100	nA	V_{DS} = 20V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	-	-	±1.0	µA	V_{GS} = ±4.5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(TH)}$	0.5	-	0.9	V	V_{DS} = V_{GS}, I_D = 250µA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	-	0.3	0.4	Ω	V_{GS} = 4.5V, I_D = 600mA
		-	0.4	0.5		V_{GS} = 2.5V, I_D = 500mA
		-	0.5	0.7		V_{GS} = 1.8V, I_D = 350mA
Diode Forward Voltage	V_{SD}	-	0.7	1.2	V	V_{GS} = 0V, I_S = 150mA,
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	-	56	-	pF	V_{DS} =16V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{oss}	-	19	-	pF	
Reverse Transfer Capacitance	C_{rss}	-	7.3	-	pF	
Gate Resistance	R_g	-	86	-	Ω	V_{DS} = 0V, V_{GS} = 0V,
Total Gate Charge (V_{GS} = 4.5V)	Q_g	-	0.6	-	nC	V_{DS} = 10V, I_D = 250mA
Total Gate Charge (V_{GS} = 10V)	Q_g	-	1.3	-	nC	
Gate-Source Charge	Q_{gs}	-	0.1	-	nC	
Gate-Drain Charge	Q_{gd}	-	0.16	-	nC	
Turn-On Delay Time	$t_{D(ON)}$	-	5.3	-	ns	V_{DD} = 10V, V_{GS} = 4.5V, R_L = 47Ω, R_g = 10Ω, I_D = 200mA
Turn-On Rise Time	t_R	-	2.6	-	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	-	18.1	-	ns	
Turn-Off Fall Time	t_F	-	6.6	-	ns	

Notes:
5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with 25mm X 25mm square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

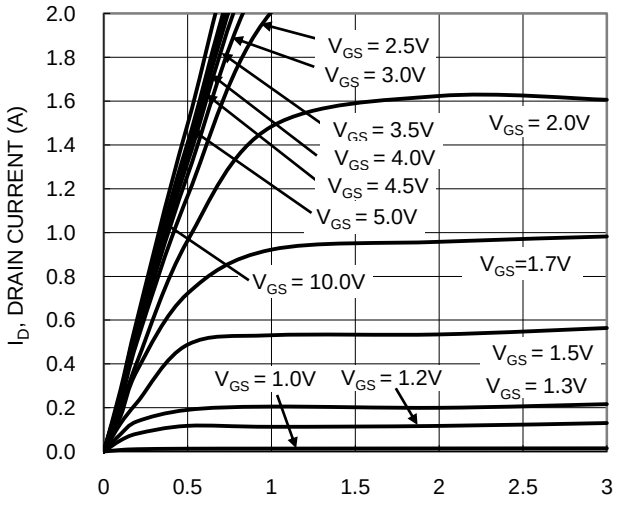


Figure 1. Typical Output Characteristic

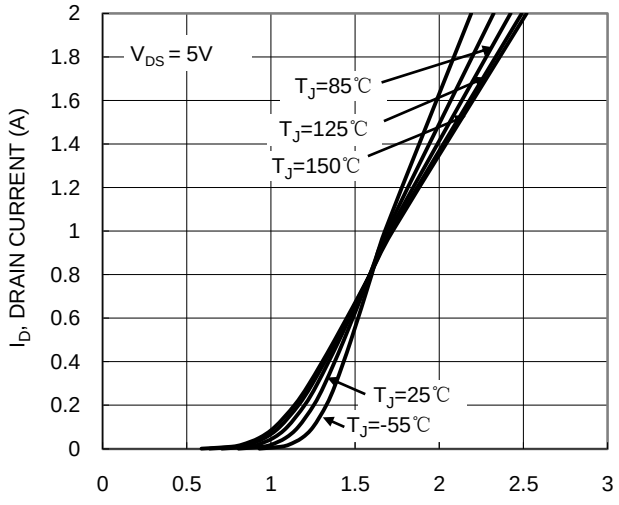


Figure 2. Typical Transfer Characteristic

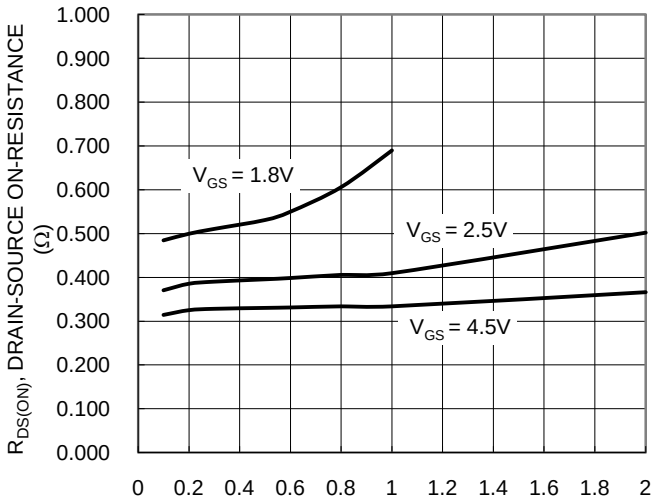


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

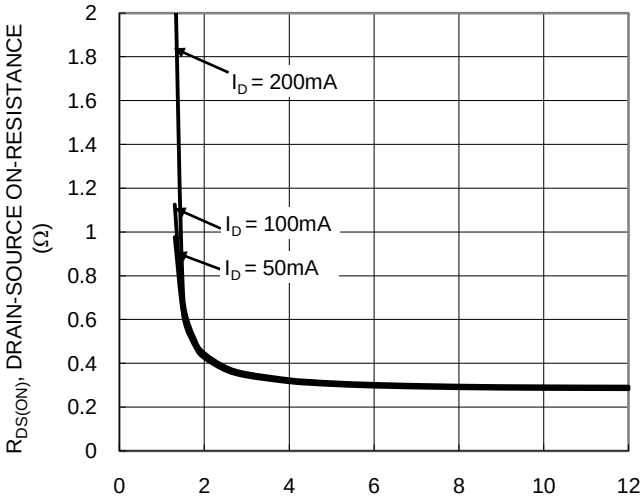


Figure 4. Typical Transfer Characteristic

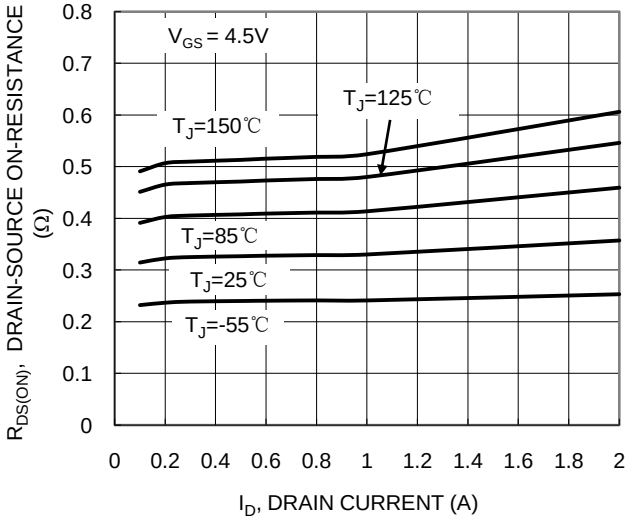


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

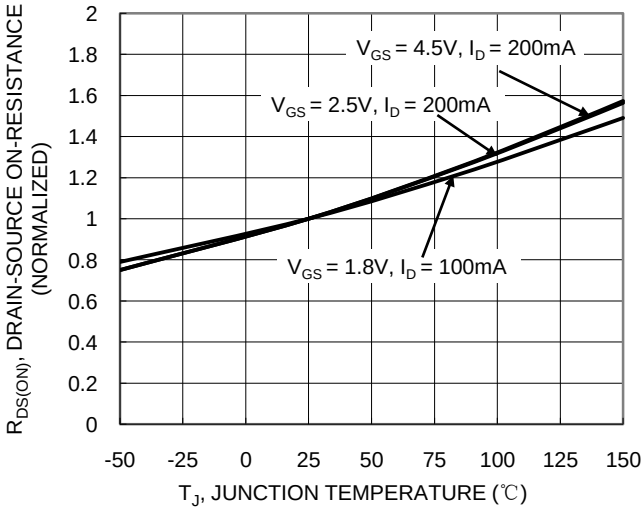


Figure 6. On-Resistance Variation with Temperature

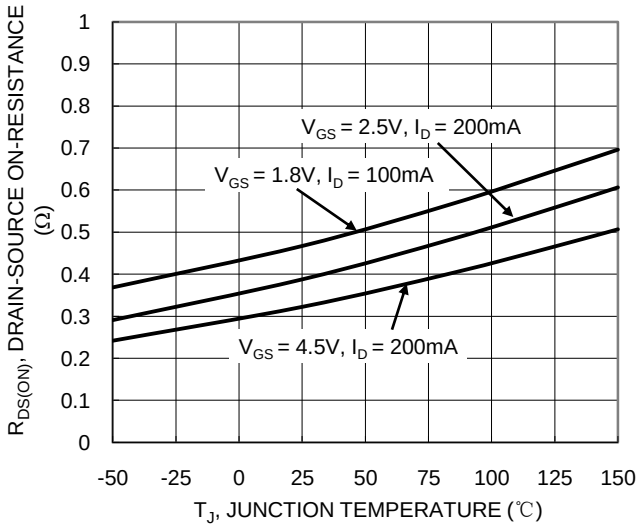


Figure 7. On-Resistance Variation with Temperature

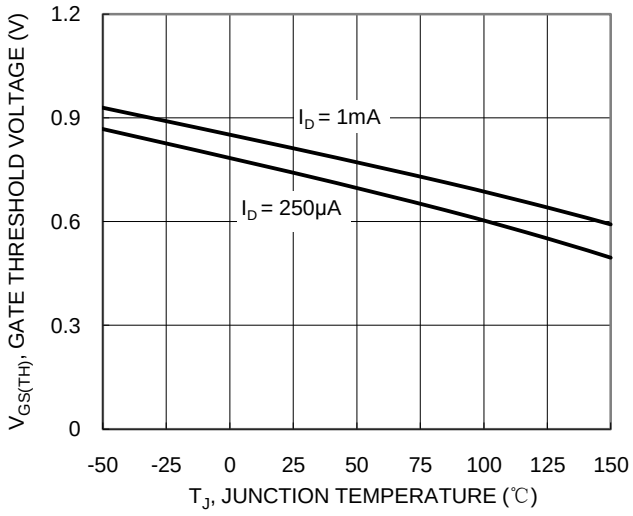


Figure 8. Gate Threshold Variation vs. Junction Temperature

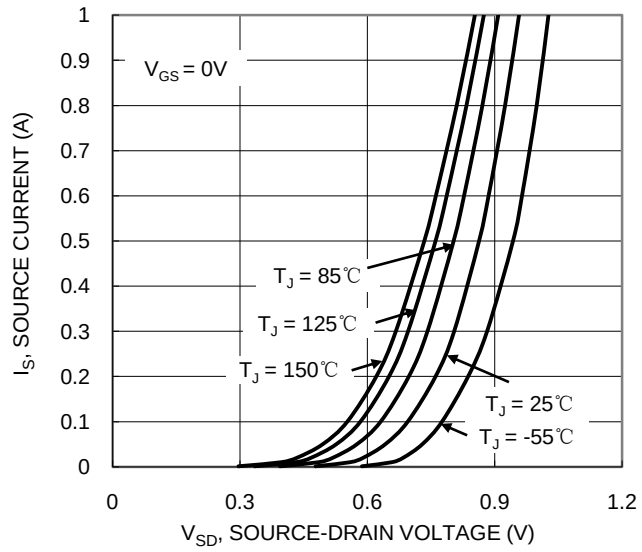


Figure 8. Diode Forward Voltage vs. Current

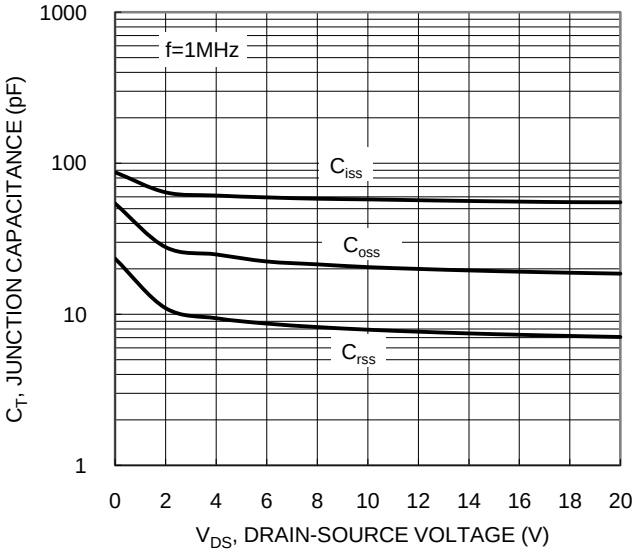


Figure 10. Typical Junction Capacitance

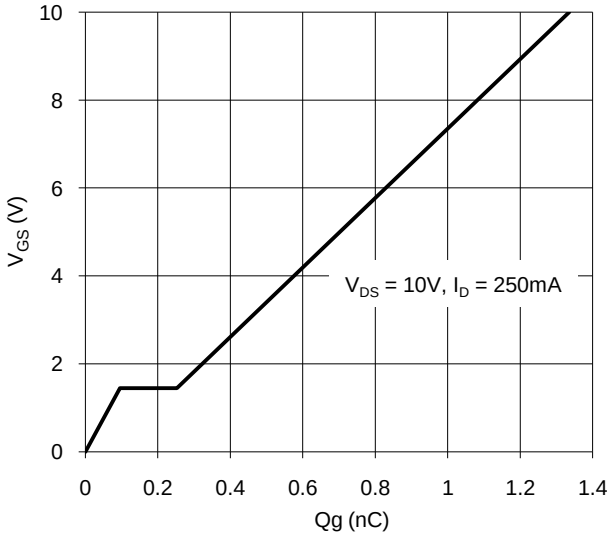


Figure 11. Gate Charge

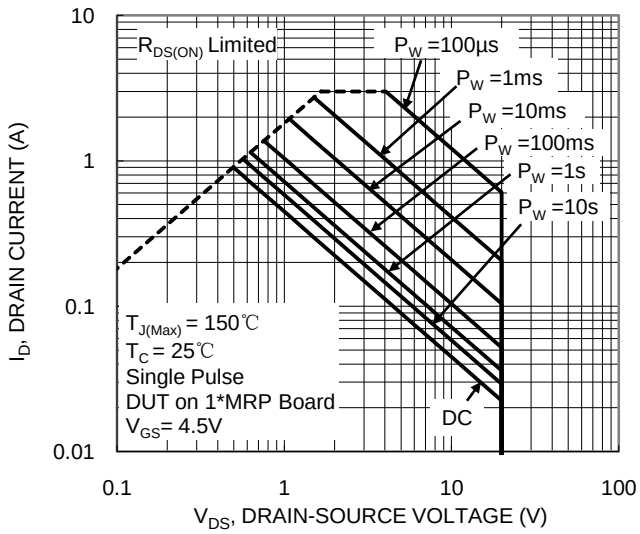


Figure 12. SOA, Safe Operation Area

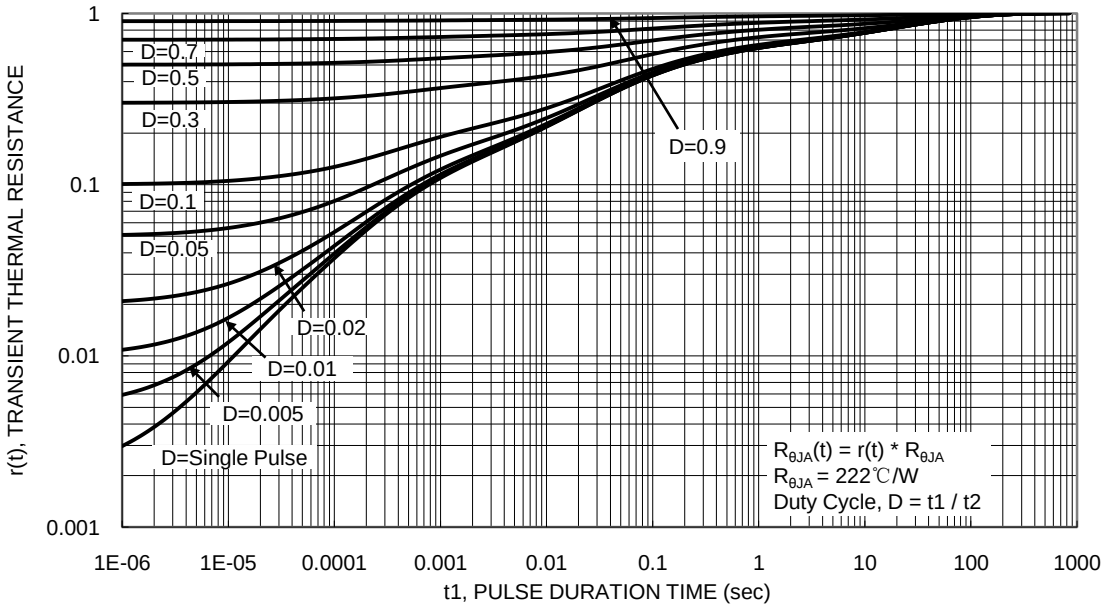
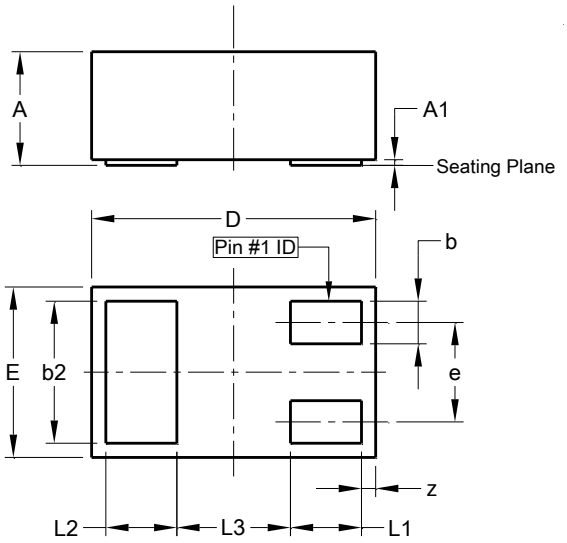


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3

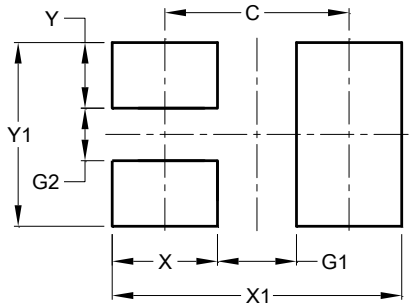


X2-DFN1006-3			
Dim	**Min**	**Max**	**Typ**
A	-	0.40	-
A1	0.00	0.05	0.03
b	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	-	-	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	-	-	0.40
z	0.02	0.08	0.05
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

X2-DFN1006-3



Dimensions	Value (in mm)
C	0.70
G1	0.30
G2	0.20
X	0.40
X1	1.10
Y	0.25
Y1	0.70